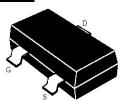
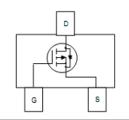
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Features

- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance

MAXIMUM RANTINGS

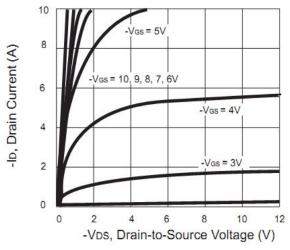
Characteristic	Symbol	Max	ux Unit	
Drain-Source Voltage	$\mathrm{BV}_{\mathrm{DSS}}$	-30	V	
Gate- Source Voltage	$ m V_{GS}$	<u>+</u> 12	V	
Drain Current (continuous)	I_D	-4.2	A	
Drain Current (pulsed)	I_{DM}	-18	A	
Total Device Dissipation TA=25°C	P_{D}	1400	mW	
Junction	T_{J}	150	$^{\circ}\!\mathbb{C}$	
Storage Temperature	T_{stg}	-55to+150	$^{\circ}\!\mathbb{C}$	

Electrical Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage (I _D = -250uA,V _{GS} =0V)	BV _{DSS}	-30			V
Gate Threshold Voltage $(I_D = -250uA, V_{GS} = V_{DS})$	V _G S(th)	-0.6	_	-2	V
Diode Forward Voltage Drop (I _S = -1 A,V _{GS} =0V)	V _{SD}	_	_	-1	V
Zero Gate Voltage Drain Current (V _{GS} =0V, V _{DS} = -24V) (V _{GS} =0V, V _{DS} = -24V,T _A =55°C)	I _{DSS}	_		-1 -5	uA
Gate Body Leakage (V _{GS} =±12V, V _{DS} =0V)	IGSS		_	<u>±</u> 100	nA
Static Drain-Source On-State Resistance (I _D = -4.1A,V _{GS} = -10V)	R _{DS(ON)}		42	50	mΩ
Static Drain-Source On-State Resistance (I _D = -2A,V _{GS} = -4.5V)	R _{DS(ON)}		53	60	mΩ
Static Drain-Source On-State Resistance (I _D = -1A,V _{GS} = -2.5V)	R _{DS(ON)}	_	80	85	mΩ
Input Capacitance (V _{GS} =0V, V _{DS} = -15V,f=1MHz)	CISS	_	954		pF
Output Capacitance (V _{GS} =0V, V _{DS} = -15V,f=1MHz)	Coss	_	115		pF
Turn-ON Time $(V_{DS}=-15V, V_{GS}=-10 V, R_{GEN}=6 \Omega)$	t(on)	_	6		ns
Turn-OFF Time $(V_{DS}=-15V, V_{GS}=-10 \text{ V}, R_{GEN}=6 \Omega)$	t(off)		38		ns

Page 1 of 3 Rev 8: Nov 2014 www.born-tw.com





25 20 -lb, Drain Current (A) Tj = 125°C 15 25°C ◀ 10 5 0 1.6 -Vgs, Gate-to-Source Voltage (V)

Fig 1: Output Characteristics 120 100 RDS(ON) (MD) 80 V_{GS}=-2.5V V_{GS}=-4.5V 60 40 V_{GS}=-10V 20 0.00 2.00 4.00 6.00 8.00 10.00 -ID (A)

Figure 2: Transfer Characteristics

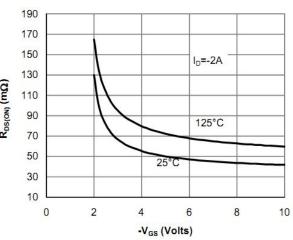
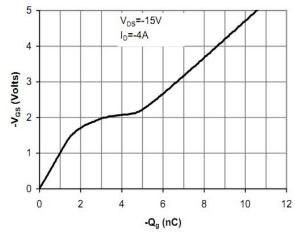


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Gate-Source Voltage



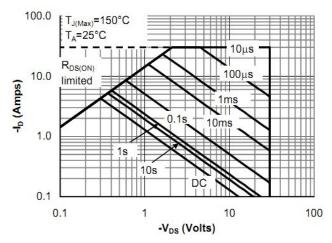


Figure 5: Gate-Charge Characteristics

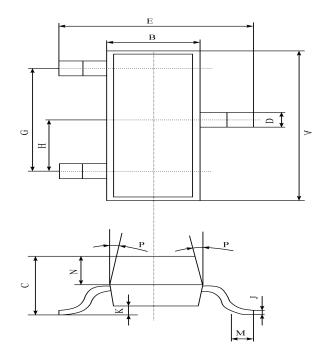
Figure 6: Safe Operating Area

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SOT-23 PACKAGE OUTLINE Plastic surface mounted package



SOT-23		
Α	2.90 ± 0.10	
В	1.30 ± 0.10	
C	1.00 ± 0.10	
D	0.40 ± 0.10	
E	2.40 ± 0.20	
G	1.90 ± 0.10	
Н	0.95 ± 0.05	
J	0.13 ± 0.05	
K	0.00-0.10	
М	≥0.2	
Z	0.60 ± 0.10	
P	7 ± 2 °	

(UNIT): mm